

09/856209

8 Rec'd PCT/PTO 1 8 MAY 2001

82822

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

3A
2/3/01

In Re U.S. Patent Application)
)
Applicant: Kozo NAKAMURA, Toshiaki)
SAISHOJI, Takashi YOKOYAMA,)
Shin MATSUKUMA, and Fumitaka)
ISHIKAWA)
)
Serial No.: Not Yet Assigned)
)
Filed: Herewith)
)
For: SILICON SINGLE CRYSTAL)
AND PRODUCTION METHOD)
FOR SILICON SINGLE)
CRYSTAL WAFER)
)

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

This is a Preliminary Amendment for entry in the above-identified application.

In the Claims:

Please amend claims as follows:

4. (once amended) The silicon single crystal ingot production method according to claim 2, characterized in that, when producing the silicon single crystal ingot, a pulling speed of the silicon single crystal ingot is changed.

5. (once amended) A silicon single crystal wafer, obtained from the silicon single crystal ingot of claim 2, wherein there exists an OSF ring an inner diameter of which is 70%

A

Sub 00